

MN74HC368/MN74HC368S

Inverting Hex TRI-STATE Buffers

■ Outline

The MN74HC368/MN74HC368S consist of high speed inverting buffers having six 3-state outputs.

Because of the large current, these buffers assure high speed operation even when driving a large capacity bus line. They have two inputs $\overline{G}1$ and $\overline{G}2$ to enable the outputs when the level is "L", and the input $\overline{G}1$ controls four gates while the input $\overline{G}2$ controls two gates.

Owing to the silicon gate CMOS process, these buffers have realized low power consumption and high noise immunity equivalent to those of a standard CMOS and the operation speed as high as of an LS TTL, and can directly drive fifteen LS TTL inputs.

To protect the input and output against electrostatic breakdown, a resistor and a diode are used for the V_{CC} and the GND. The pin configuration and the function are the same as those of the standard 54LS/74LS logic family.

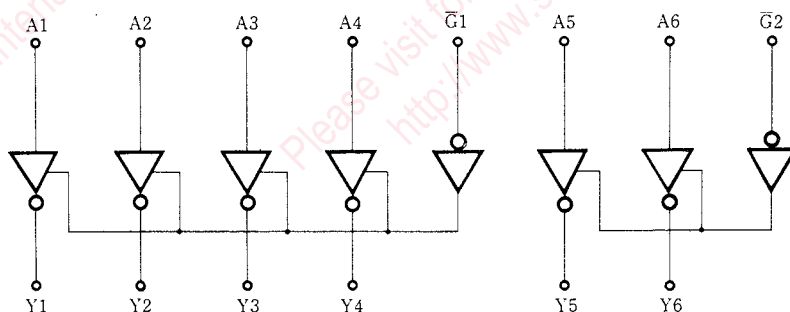
■ Truth Table

Input		Output
\overline{G}	A	Y
H	X	Hi-Z
L	H	L
L	L	H

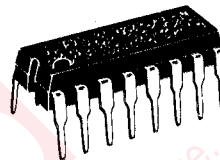
Note 1. Hiz : High impedance

2. x : "H" or "L" either will do.

■ Logic Diagram



P-3



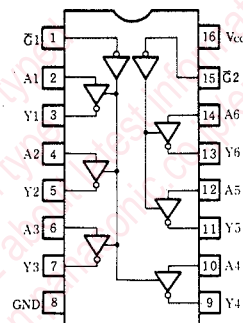
16-pin plastic DIL package

P-4



16-pin PANAFLAT package (SO-16D)

Pin Configuration



■ Absolute Maximum Ratings

Item			Symbol	Rating	Unit
Supply voltage			V_{CC}	$-0.5 \sim +7.0$	V
Input output voltage			V_I, V_O	$-0.5 \sim V_{CC} + 0.5$	V
Input protective diode current			I_{IK}	± 20	mA
Output parasitic diode current			I_{OK}	± 20	mA
Output current			I_O	± 35	mA
Supply current			I_{CC}, I_{GND}	± 70	mA
Storage temperature			T_{SR}	$-65 \sim +150$	°C
Power dissipation	MN74HC368	$T_a = -40 \sim +60^\circ\text{C}$	P_D	400	mW
		$T_a = +60 \sim +85^\circ\text{C}$		Decrease to 200mW at the rate of 8mW/°C	
	MN74HC368S	$T_a = -40 \sim +60^\circ\text{C}$	P_D	275	mW
		$T_a = +60 \sim +85^\circ\text{C}$		Decrease to 200mW at the rate of 3.8mW/°C	

■ Recommended Operating Conditions

Item		Symbol	$V_{CC}(V)$	Rating	Unit
Operating power supply voltage		V_{CC}		$1.4 \sim 6.0$	V
Input output voltage		V_I, V_O		$0 \sim V_{CC}$	V
Operating temperature		T_A		$-40 \sim +85$	°C
Input rise, fall time		t_r, t_f	2.0	$0 \sim 1000$	ns
			4.5	$0 \sim 500$	ns
			6.0	$0 \sim 400$	ns

■ DC Characteristics (GND=0V)

Item	Symbol	V _{CC} (V)	Test Condition			Temperature					Unit
			V _I	V _O	Unit	Ta=25°C			Ta=-40~+85°C		
						min.	typ.	max.	min.	max.	
Input voltage high level	V _{IH}	2.0				1.5			1.5		V
		4.5				3.15			3.15		
		6.0				4.2			4.2		
Input voltage low level	V _{IL}	2.0						0.3		0.3	V
		4.5						0.9		0.9	
		6.0						1.2		1.2	
Output voltage high level	V _{OH}	2.0		-20.0	μA	1.9	2.0		1.9		V
		4.5	V _{IH}	-20.0	μA	4.4	4.5		4.4		
		6.0	or	-20.0	μA	5.9	6.0		5.9		
		4.5	V _{IL}	-6.0	mA	3.92			3.84		
		6.0		-7.8	mA	5.48			5.34		
Output voltage low level	V _{OL}	2.0		20.0	μA		0.0	0.1		0.1	V
		4.5	V _{IH}	20.0	μA		0.0	0.1		0.1	
		6.0	or	20.0	μA		0.0	0.1		0.1	
		4.5	V _{IL}	6.0	mA			0.26		0.33	
		6.0		7.8	mA			0.26		0.33	
Input leakage current	I _I	6.0	V _I =V _{CC} or GND					±0.1		±1.0	μA
3-state output OFF leakage current	I _{OZ}	6.0	V _I =V _{IH} or V _{IL} V _O =V _{CC} or GND					±0.5		±5.0	μA
Static supply current	I _{CC}	6.0	V _I =V _{CC} or GND, I _O =0					8.0		80.0	μA

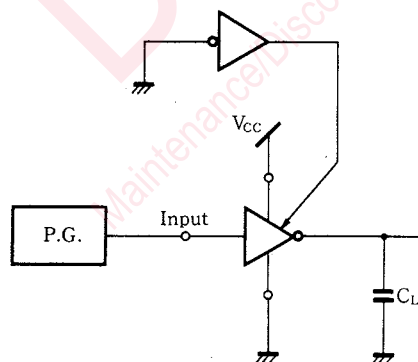
■ AC Characteristics (GND=0V, Input transition time $\leq 6\text{ns}$, $C_L=50\text{pF}$)

Item	Symbol	V _{CC} (V)	Test Condition	Temperature					Unit
				Ta=25°C			Ta=-40~+85°C		
				min.	typ.	max.	min.	max.	
Output rise time	t _{TLH}	2.0			19	75		95	ns
		4.5			7	15		19	
		6.0			6	13		16	
Output fall time	t _{THL}	2.0			10	75		95	ns
		4.5			5	15		19	
		6.0			4	13		16	
Propagation time (L→H)	t _{PLH}	2.0			18	75		95	ns
		4.5			9	15		19	
		6.0			7	13		16	
Propagation time (H→L)	t _{PHL}	2.0			15	75		95	ns
		4.5			7	15		19	
		6.0			6	13		16	
3-state propagation time (H→Z)	t _{PHZ}	2.0	R _L =1kΩ		18	125		155	ns
		4.5			13	25		31	
		6.0			12	21		26	
3-state propagation time (L→Z)	t _{PLZ}	2.0	R _L =1kΩ		18	125		155	ns
		4.5			11	25		31	
		6.0			10	21		26	
3-state propagation time (Z→H)	t _{PZH}	2.0	R _L =1kΩ		21	100		125	ns
		4.5			10	20		25	
		6.0			8	17		21	
3-state propagation time (Z→L)	t _{PZL}	2.0	R _L =1kΩ		24	100		125	ns
		4.5			10	20		25	
		6.0			8	17		21	

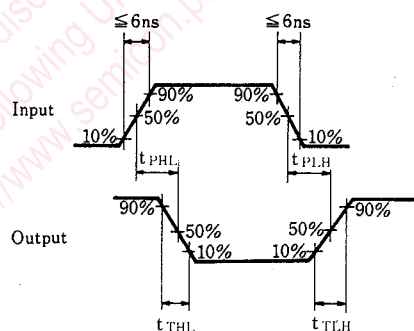
● Switching time measuring circuit and waveforms

(1) t_{TLH} , t_{THL} , t_{PLH} , t_{PHL}

1. Measuring circuit

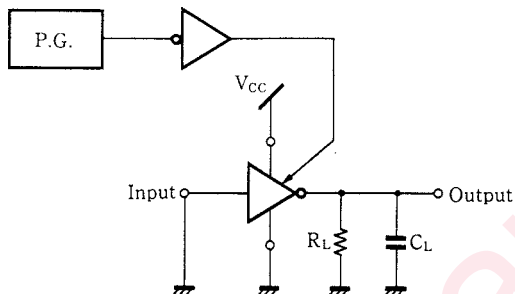


2. Switching waveforms

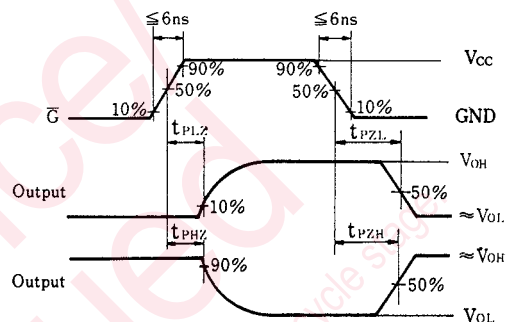


(2) t_{PHZ} , t_{PZH}

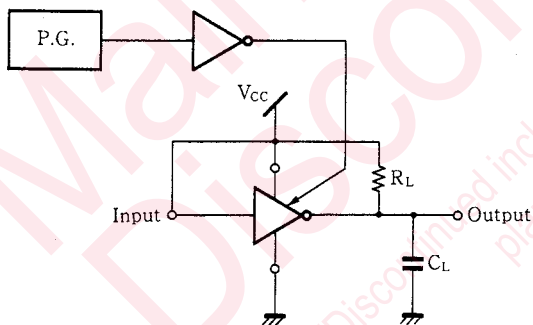
1. Measuring circuit



2. Switching waveforms

(3) t_{PLZ} , t_{PZL}

1. Measuring circuit



2. Switching waveforms

See above (2) 2 for waveforms.

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